

**In the Specification:**

Please insert before the first paragraph of the application:

This application is the national stage application of international application number PCT/DE03/003129, filed on September 19, 2003, which claims the benefit of priority to German Patent Application 102 45 152.4, filed on September 27, 2002, incorporated herein by reference.

Please delete the paragraph on page 1, lines 30-33.

Please rewrite the paragraph on page 3, lines 3-8.

- interconnects which preferably ~~contain a metal or~~ comprise a metal, and/or which are in each case led into another metallization layer or metallization plane by means of at least one via or contact hole which particularly influences the reliability,

Please rewrite the paragraph on page 4, lines 10-21.

In a next development of the circuit arrangement according to the invention, the heating element is a resistance heating element which preferably ~~contains polycrystalline silicon or~~ comprises polycrystalline silicon. In order to set the conductivity of the polycrystalline silicon, it is doped. However, other developments also make use of heating elements which ~~contain a metal or~~ comprise a metal. If the heating element is fed with AC current, then it is possible to prevent or considerably reduce degradation processes, e.g. electromigration in particular in heating elements made of metal.